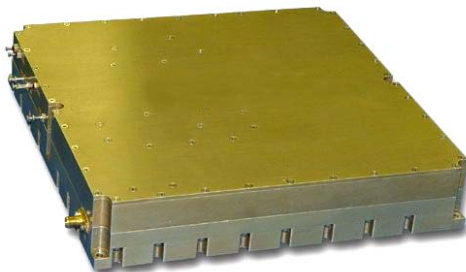


ZHM 800-2500/50 MIL GRADE HIGH POWER AMPLIFIER 800 MHz TO 2.5 GHz



This is a high power, broadband, silicon carbide (SiC) RF amplifier that operates from 0.8 to 2.5 GHz. This PA is ideal for broadband military platforms as well as commercial applications. It is packaged in a modular housing that is approximately 8.0" by 8.0" by 1.5". This amplifier has a typical P3dB of 70 watts at room temperature. Noise figure at room temperature is 10.0 dB typical. This amplifier offers a typical gain of 45 dB with a typical gain flatness of ± 2.0 dB. Typical OIP3 is 58 dBm. Input and Output VSWR is 2.0:1 maximum. Class AB current is ~6.3 amps typical employing a +50 Vdc supply. This amplifier operates from -40C to +85C base plate temperature.

- Silicon Carbide Broadband Power Amplifier
- Operation from 800 MHz to 2.5 GHz min
- Small Signal Gain 45 dB typical
- 58 dBm OIP3 typ
- 70 Watts P3dB typ

Freq (MHz)	Small Signal Gain (dB)	P3dB (dBm)	Pin at P3dB (dBm)	Current @ P3dB from @ 50Vdc Supply (Amps)	2nd Harmonic @ P3dB (dBc)	3rd Harmonic @ P3dB (dBc)
0.80	44.3	48.3	6.4	6.9	-32.0	-46.0
1.00	44.4	49.6	7.8	7.5	-36.0	-54.0
1.20	46.1	49.3	5.5	8.4	-45.0	-63.0
1.40	45.6	48.3	5.0	8.6	-56.0	-62.0
1.60	45.0	48.2	6.1	8.5	-47.0	-51.0
1.80	44.2	48.3	7.7	8.7	-50.0	-57.0
2.00	40.6	48.0	10.0	9.0	-55.0	-60.0
2.20	45.1	48.1	6.5	8.7	-55.0	-60.0
2.40	42.6	47.9	9.6	8.5	-48.0	-60.0
2.50	42.6	47.9	8.9	8.4	-50.0	-60.0